

PSMN039-100YS

N-channel LFPAK 100 V 39.5 m Ω standard level MOSFET

Rev. 02 — 2 April 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	28.1	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	74	W
Tj	junction temperature		-55	-	175	°C
Avalanci	he ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;}$ $I_{D} = 28.1 \text{ A; } V_{sup} \le 100 \text{ V;}$ unclamped; $R_{GS} = 50 \Omega$	-	-	42	mJ
Dynamic characteristics						
Q_GD	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$	-	8	-	nC
$Q_{G(tot)} \\$	total gate charge	V _{DS} = 50 V; see <u>Figure 14</u> and <u>15</u>	-	23	-	nC



Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{ or } 12}$	-	-	71 r	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{\text{Figure } 13}$	-	30.8	39.5	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	[q]	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 \$
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN039-100YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	20	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	28.1	Α
I _{DM}	peak drain current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; \text{ T}_{\text{mb}} = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 3}}{}$	-	112	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	74	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dr	ain diode				
Is	source current	T _{mb} = 25 °C	-	28.1	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	112	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 28.1 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	42	mJ

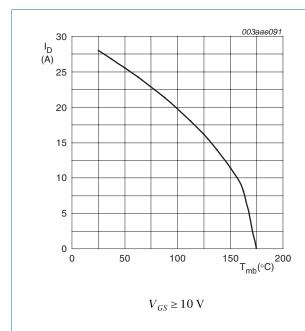


Fig 1. Continuous drain current as a function of mounting base temperature

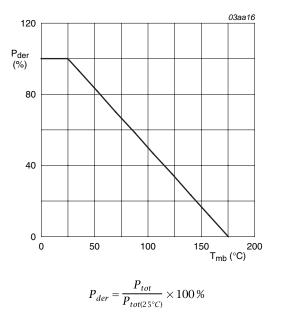
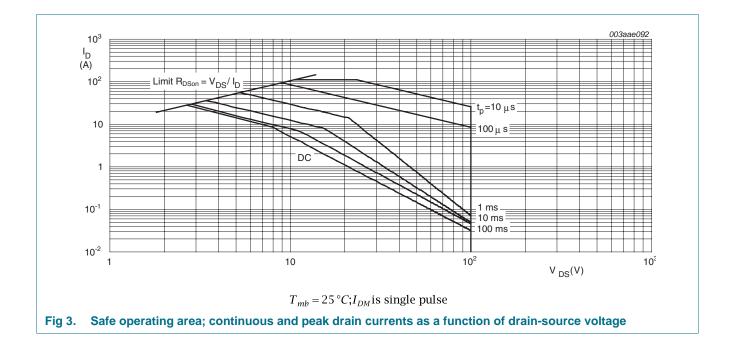


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1	2.03	K/W

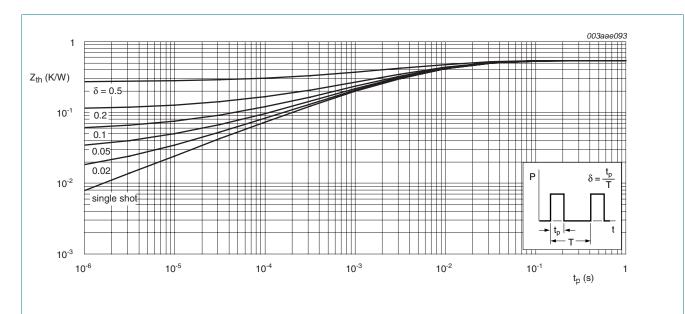


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source		$I_D = 0.25 \text{ mA}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}\text{C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
()	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 11</u> and <u>10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.7	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.01	2	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	71	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	72.9	100	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	30.8	39.5	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	0.62	1.5	Ω
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 15 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14 and 15	-	23	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	19	-	nC
Q_{GS}	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14	-	3	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2	-	nC
Q_{GD}	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	8	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$; see Figure 14 and 15	-	4.5	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1847	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	86	-	pF
C _{rss}	reverse transfer capacitance		-	64	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 3.3 \Omega; V_{GS} = 10 \text{ V};$	-	11	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	8	-	ns
t _{d(off)}	turn-off delay time		-	22	-	ns
t _f	fall time		-	7	-	ns

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Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	44	-	ns
Qr	recovered charge	$V_{DS} = 50 \text{ V}$	-	78	-	nC

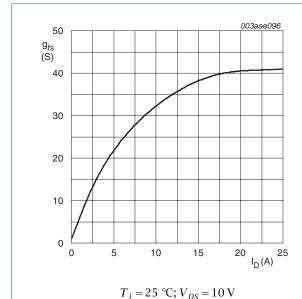


Fig 5. Forward transconductance as a function of drain current; typical values

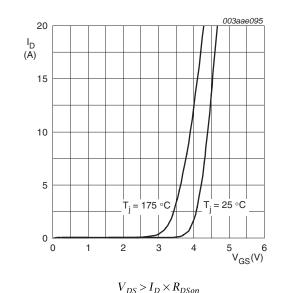


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

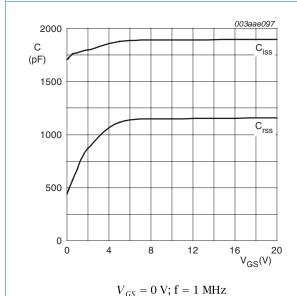
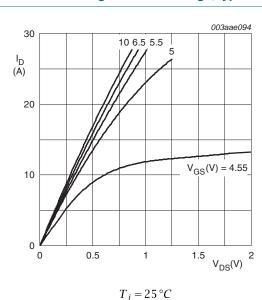


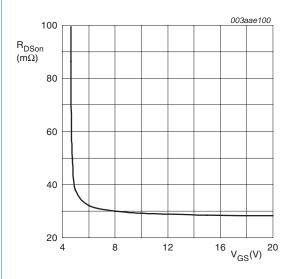
Fig 7. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



Output characteristics: drain current as a Fig 8. function of drain-source voltage; typical values

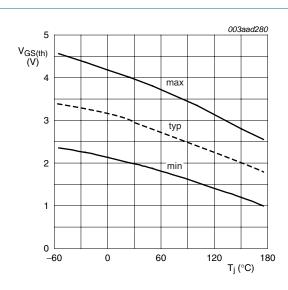
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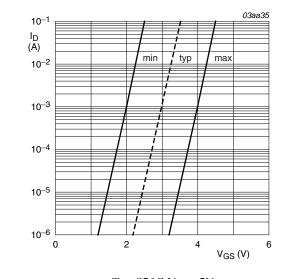
 $T_j = 25$ °C; $I_D = 15$ A

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$I_D = 1$$
 mA; $V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage

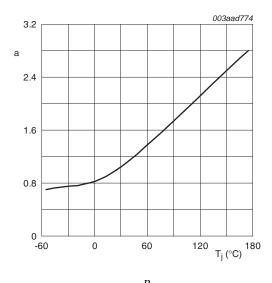


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

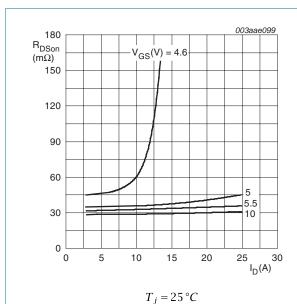


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

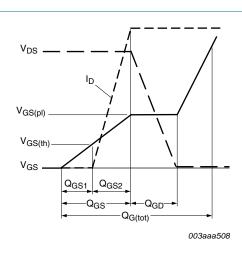


Fig 14. Gate charge waveform definitions

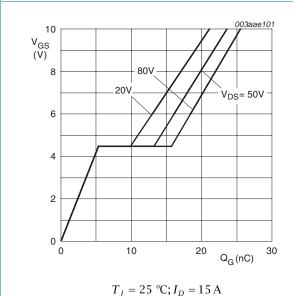


Fig 15. Gate-source voltage as a function of gate charge; typical values

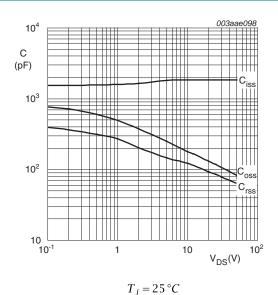


Fig 16. Drain-source on-state resistance as a function of drain current; typical values

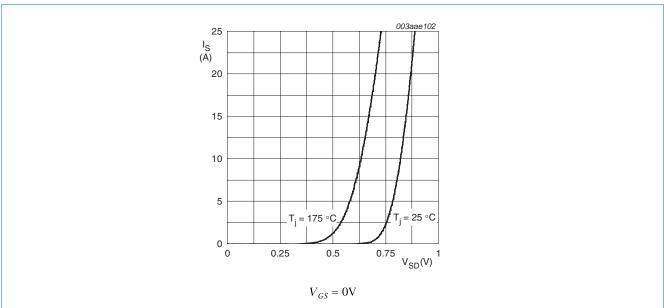


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669

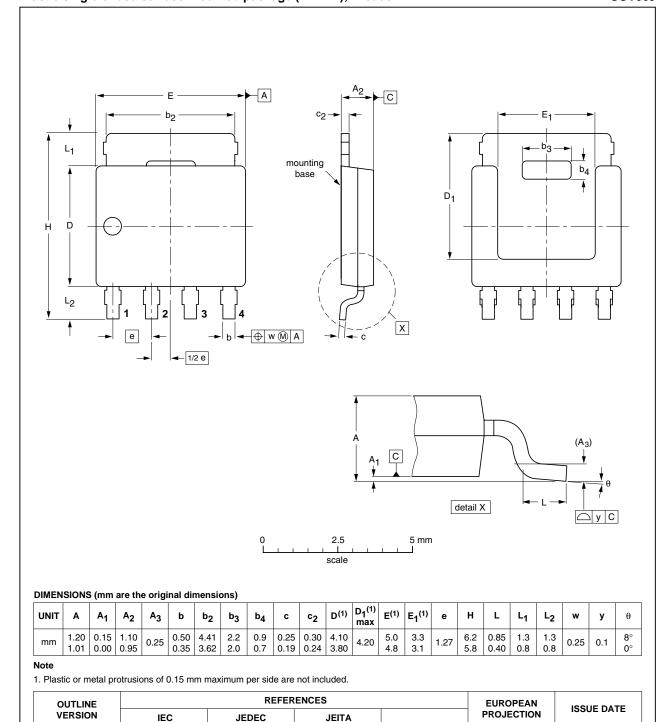


Fig 18. Package outline SOT669 (LFPAK)

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04-10-13

06-03-16

SOT669

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN039-100YS_2	20100402	Product data sheet	-	PSMN039-100YS_1
Modifications: • Status changed from Objective to Product.				
PSMN039-100YS_1	20100114	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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N-channel LFPAK 100 V 39.5 mΩ standard level MOSFET

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